

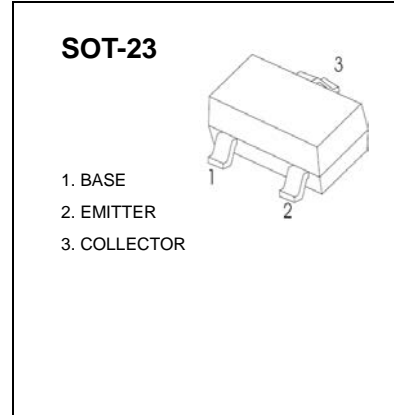


## Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

### FEATURES

- High DC current gain
- Complementary to KTA1298



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	35	V
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	800	mA
$P_C$	Collector Power Dissipation	200	mW
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=30\text{V}, I_E=0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=20\text{mA}$			0.5	V
base-emitter voltage	$V_{BE}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	0.5		0.8	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

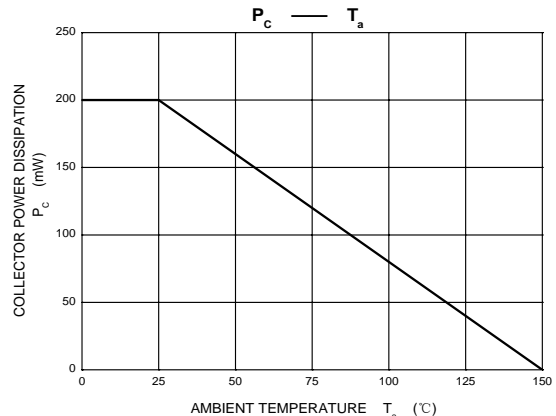
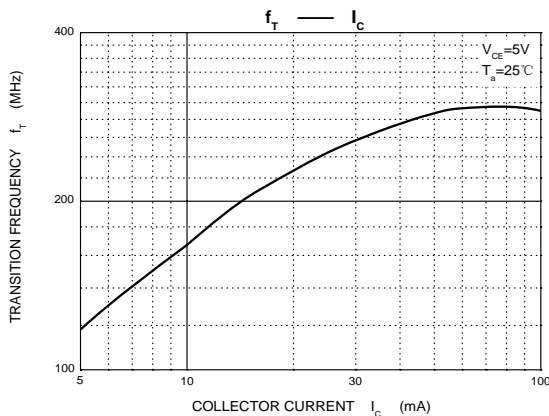
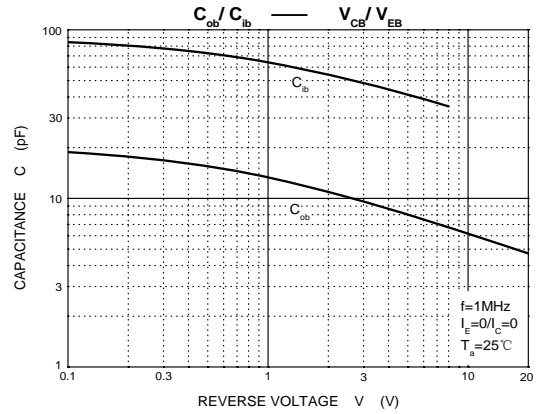
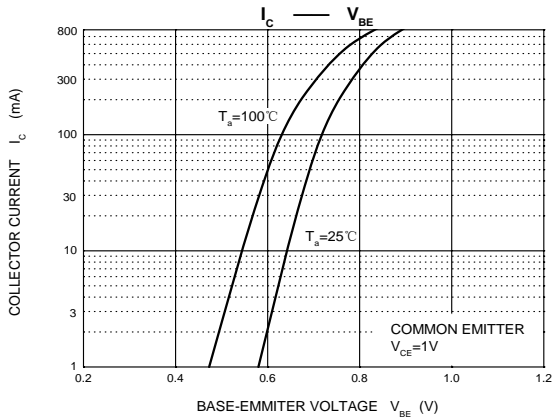
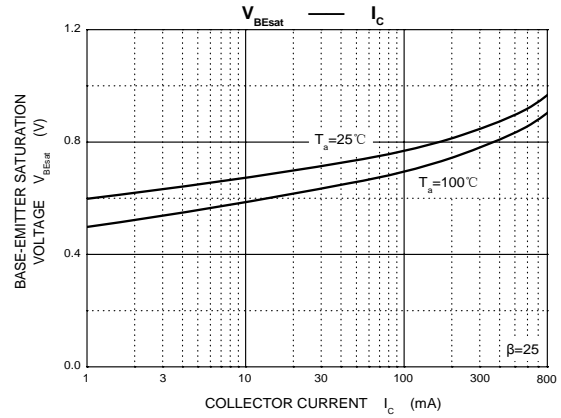
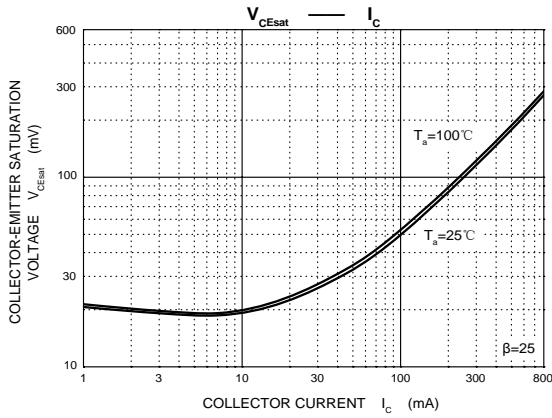
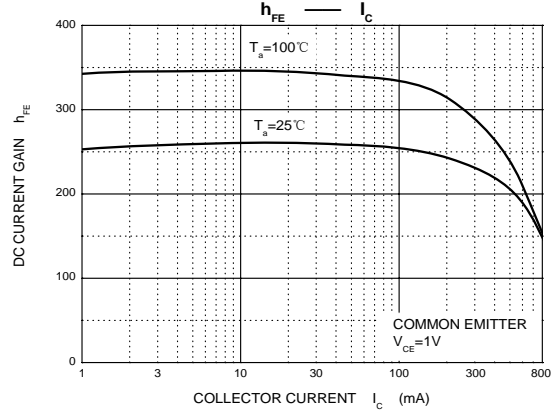
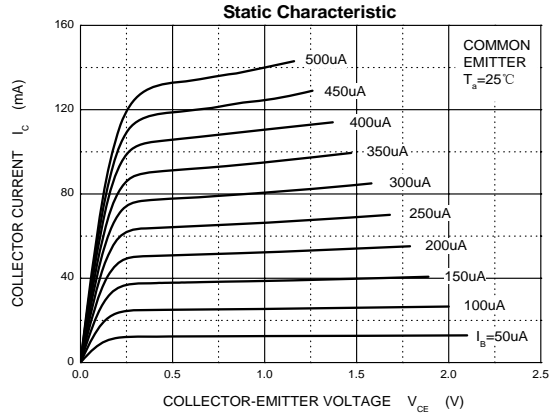
### CLASSIFICATION OF $h_{FE}$

Rank	O	Y
Range	100-200	160-320
Marking	EO	EY



## Typical Characteristics

## KTC3265

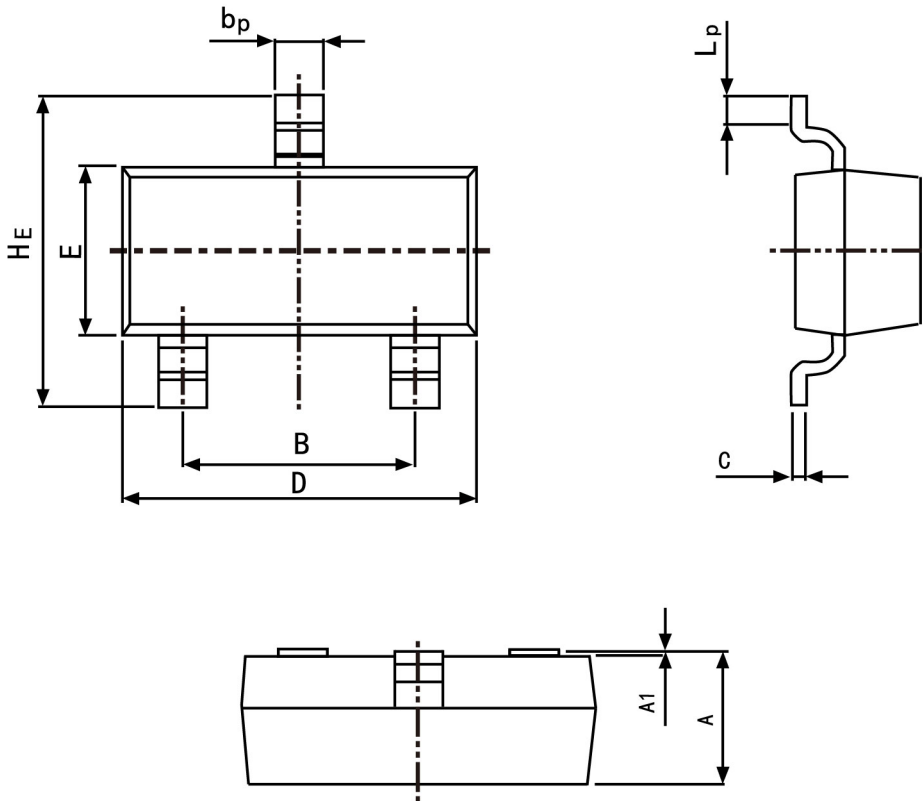




## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
$b_p$	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
$A_1$	0.100	0.013
$L_p$	0.20	0.50